

# +5 V Fixed, Adjustable Micropower Linear Voltage Regulators

# ADM663/ADM666

#### **FEATURES**

5 V Fixed or +1.3 V to +16 V Adjustable Low Power CMOS: 12 µA max Quiescent Current 40 mA Output Current Current Limiting Pin Compatible with MAX663/666 +2 V to +16.5 V Operating Range Low Battery Detector ADM666 No Overshoot on Power-Up

APPLICATIONS
Handheld Instruments
LCD Display Systems
Pagers
Remote Data Acquisition

#### **GENERAL DESCRIPTION**

The ADM 663/ADM 666 are precision voltage regulators featuring a maximum quiescent current of 12  $\mu A$ . They can be used to give a fixed +5 V output with no additional external components or can be adjusted from 1.3 V to 16 V using two external resistors. Fixed or adjustable operation is automatically selected via the V\_{SET} input. The low quiescent current makes these devices especially suitable for battery powered systems. The input voltage range is 2 V to 16.5 V and an output current up to 40 mA is provided. The ADM 663 can directly drive an external pass transistor for currents in excess of 40 mA. Additional features include current limiting and low power shutdown. Thermal shutdown circuitry is also included for additional safety.

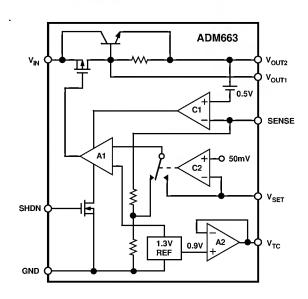
The ADM 666 features additional low battery monitoring circuitry to detect for low battery voltages.

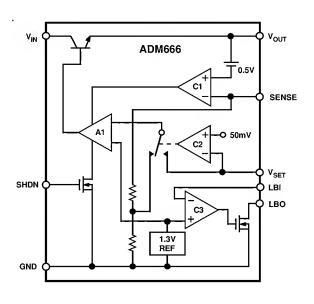
The ADM 663/ADM 666 are pin-compatible replacements for the MAX 663/666. Both are available in 8-pin DIP and in narrow surface mount (SOIC) packages.

#### **ORDERING GUIDE**

Model	Temperature Range	Package Option	
AD M 663AN	-40°C to +85°C	N -8	
ADM 663AR	-40°C to +85°C	R-8	
ADM 666AN	-40°C to +85°C	N-8	
ADM 666AR	-40°C to +85°C	R-8	

#### **FUNCTIONAL BLOCK DIAGRAMS**





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# ADM663/ADM666- SPECIFICATIONS (VIN = +9 V, VOUT = + 5 V, TA = + 25°C unless otherwise noted)

Parameter	Min	Тур	Max	Units	Test Conditions/Comments
Input Voltage, V <sub>IN</sub>	2.0		16.5	V	$T_A = T_{MIN}$ to $T_{MAX}$
Quiescent Current, I <sub>Q</sub>					No Load, $V_{IN} = +16.5 \text{ V}$
		6	12	μΑ	$T_A = +25$ °C
			15	μA	$T_A = T_{MIN}$ to $T_{MAX}$
Output Voltage, V <sub>OUT</sub>	4.75	5.0	5.25	V	$T_A = T_{MIN}$ to $T_{MAX}$ , $V_{SET} = GND$
Line Regulation, ΔV <sub>OUT</sub> /ΔV <sub>IN</sub>		0.03	0.35	%/V	$+2 \text{ V} \leq \text{V}_{\text{IN}} \leq +15 \text{ V}, \text{ V}_{\text{OUT}} = \text{V}_{\text{REF}}$
Load Regulation, $\Delta V_{OUT}/\Delta I_{OUT}$		3.0	7.0	Ω	AD M 663, 1 mA $\leq I_{OUT2} \leq 20$ mA
		1.0	5.0	Ω	ADM 663, 50 $\mu$ A $\leq I_{OUT1} \leq 5$ mA
		3.0	7.0	Ω	ADM 666, 1 mA $\leq$ I <sub>OUT</sub> $\leq$ 20 mA
Reference Voltage, V <sub>SET</sub>	1.27	. 100	1.33	V	$V_{OUT} = V_{SET}$
Reference T empco, $\Delta V_{SET}/\Delta T$		$\pm 100$		ppm/°C	$T_A = T_{MIN}$ to $T_{MAX}$
V <sub>SET</sub> Internal Threshold, V <sub>F/A</sub>		50		mV	$V_{SET} < V_{F/A}$ for +5 V Out;
V Input Current I		. 0. 01	. 10	n 1	$V_{SET} > V_{F/A}$ for Adj. Out
V <sub>SET</sub> Input Current, I <sub>SET</sub> Shutdown Input Voltage, V <sub>SHDN</sub>	1.4	$\pm 0.01$	$\pm 10$	nA V	$T_A = T_{MIN}$ to $T_{MAX}$
Silutuowii iliput voitage, v <sub>SHDN</sub>	1.4		0.3	V	V <sub>SHDN</sub> High = Output Off V <sub>SHDN</sub> Low = Output On
Shutdown Input Current, I <sub>SHDN</sub>		$\pm 0.01$	±10	nA	V SH DN LOW — Output Off
SENSE Input Threshold, V <sub>OUT</sub> -V <sub>SENSE</sub>		0.5	± 10	V	Current Limit Threshold
SENSE Input Resistance, R <sub>SENSE</sub>		3		MΩ	Carrette Emilie i mesnora
Input-Output Saturation Resistance, R <sub>SAT</sub>		3		171 32	
ADM 663 V <sub>OUT 1</sub>		200	500	Ω	$V_{IN} = +2 \text{ V, } I_{OUT} = 1 \text{ mA}$
7.51. 333 10011		70	150	Ω	$V_{IN} = +9 \text{ V}, I_{OUT} = 2 \text{ mA}$
		50	150	Ω	$V_{IN} = +15 \text{ V}, I_{OUT} = 5 \text{ mA}$
Output Current from V <sub>OUT(2)</sub> , I <sub>OUT</sub>	40			mA	$+3 \text{ V} \le \text{V}_{IN} \le +16.5 \text{ V}, \text{V}_{IN} - \text{V}_{OUT} = +1.5 \text{ V}$
M inimum L oad C urrent, I <sub>L (MIN)</sub>			1.0	μА	$T_A = +25$ °C
, (//////			5.0	μA	$T_A = T_{MIN}$ to $T_{MAX}$
LBI Input Threshold, V <sub>LBI</sub>	1.21	1.28	1.37	V	ADM 666
LBI Input Current, I <sub>LBI</sub>		$\pm0.01$	$\pm 10$	nA	ADM 666
LBO Output Saturation Resistance, R <sub>SAT</sub>		35	100	Ω	$ADM 666, I_{SAT} = 2 mA$
LBO Output Leakage Current		10		nA	ADM 666, LBI = 1.4 V
V <sub>TC</sub> Open Circuit Voltage, V <sub>TC</sub>		0.9		V	ADM 663
$V_{TC}$ Sink Current, $I_{TC}$	2.0	8.0		mA	ADM 663
V <sub>TC</sub> T emperature C oefficient		+2.5		mV/°C	ADM 663

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS*
$(T_A = +25^{\circ}C \text{ unless otherwise noted})$
Input Voltage, V <sub>IN</sub> +18 V
T erminal Voltage
(ADM 663) Pins 1, 3, 5, 6, 7
(GND - $0.3 \text{ V}$ ) to ( $V_{IN} + 0.3 \text{ V}$ )
(ADM 666) Pins 1, 2, 3, 5, 6
(GND - $0.3 \text{ V}$ ) to ( $V_{IN} + 0.3 \text{ V}$ )
$(ADM 663) Pin 2 \dots (GND - 0.3 V) to (V_{OUT1} + 0.3 V)$
(ADM 666) Pin 7 (GND - 0.3 V) to +16.5 V
Output Source Current
(ADM 663, ADM 666) Pin 2 50 mA
(ADM 663) Pin 3 25 mA
Output Sink Current,
(ADM 663, ADM 666) Pin 720 mA

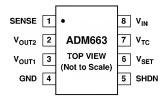
625 mW
. 120°C/W
450 mW
. 170°C/W
C to +85°C
to +150°C
+300°C
+215°C
+220°C
>5000 V

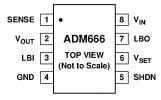
<sup>\*</sup>T his is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

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## ADM663/ADM666

#### **DIP & SOIC PIN CONFIGURATIONS**





#### PIN FUNCTION DESCRIPTION

Mnemonic	Function
V <sub>OUT(1)(2)</sub>	Voltage Regulator Output(s)
$V_{IN}$	Voltage Regulator Input
SENSE	Current Limit Sense Input. (Referenced to
	$V_{OUT(2)}$ .) If not used it should be connected to $V_{OUT(2)}$
GND	Ground Pin. M ust be connected to 0 V
LBI	Low Battery Detect Input. Compared with 1.3 V
LBO	Low Battery Detect Output. Open Drain Output
SHDN	Digital Input. May be used to disable the device so that the power consumption is minimized
$V_{SET}$	Voltage Setting Input. Connect to GND for +5 V output or connect to resistive divider for adjust able output
$V_{TC}$	T emperature-Proportional Voltage for negative TC Output

#### **GENERAL INFORMATION**

The ADM 663/ADM 666 contains a micropower bandgap reference voltage source, an error amplifier A1, two comparators C1, C2 and a series pass output transistor. A P-channel FET and an NPN transistor are used on the ADM 663 while the ADM 666 uses an NPN output transistor.

#### **CIRCUIT DESCRIPTION**

The internal bandgap reference is trimmed to 1.3 V  $\pm$  30 mV. This is used as a reference input to the error amplifier A1. The feedback signal from the regulator output is supplied to the other input by an on-chip voltage divider or by two external resistors. When V<sub>SET</sub> is at ground, the internal divider provides the error amplifier's feedback signal giving a +5 V output. When V<sub>SET</sub> is at more than 50 mV above ground, the error amplifier's input is switched directly to the V<sub>SET</sub> pin, and external resistors are used to set the output voltage. The external resistors are selected so that the desired output voltage gives 1.3 V at V<sub>SET</sub>.

Comparator C1 monitors the output current via the SEN SE input. This input, referenced to  $V_{\text{OUT}(2)}$ , monitors the voltage drop across a load sense resistor. If the voltage drop exceeds 0.5 V, then the error amplifier  $A_1$  is disabled and the output current is limited.

The ADM 663 has an additional amplifier, A2, which provides a temperature-proportional output,  $V_{TC}$ . If this is summed into the inverting input of the error amplifier, a negative temperature coefficient results at the output. This is useful when powering liquid crystal displays over wide temperature ranges.

The ADM 666 has an additional comparator, C3 which compares the voltage on the Low Battery Input, LBI, pin to the internal +1.3 V reference. The output from the comparator drives

an open drain FET connected to the Low Battery Output pin, LBO. The Low Battery Threshold may be set using a suitable voltage divider connected to LBI. When the voltage on LBI falls below 1.3 V, the open drain output LBO is pulled low.

Both the ADM 663 and the ADM 666 contain a shutdown (SHDN) input which can be used to disable the error amplifier and hence the voltage output. The quiescent current in shutdown is less than 12  $\mu$ A.

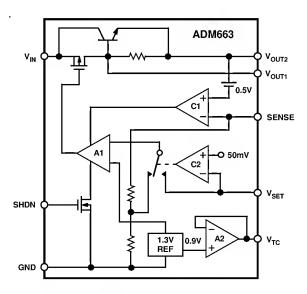


Figure 1. ADM 663 Functional Block Diagram

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### ADM663/ADM666

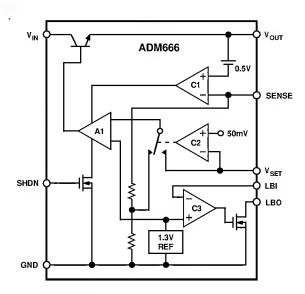


Figure 2. ADM 666 Functional Block Diagram

#### **Circuit Configurations**

For a fixed +5 V output the V<sub>SET</sub> input is grounded and no external resistors are necessary. This basic configuration is shown in Figure 3. Current limiting is not being utilized so the SENSE input is connected to V<sub>OUT(2)</sub>. The input voltage can range from +6 V to +16 V and output currents up to 40 mA are available provided that the maximum package power dissipation is not exceeded.

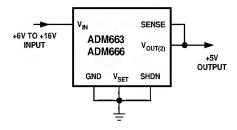


Figure 3. ADM 663/ADM 666 Fixed +5 V Output

#### **Output Voltage Setting**

If  $V_{\text{SET}}$  is not connected to  $G\,N\,D$  , the output voltage is set according to the following equation.

$$V_{OUT} = V_{SET} \times \frac{R1 + R2}{R1}$$
 where  $V_{SET} = 1.30$  V

The resistor values may be selected by firstly choosing a value for R1 and then selecting R2 according to the following equation.

$$R2 = R1 \times \left(\frac{V_{OUT}}{1.30} - 1\right)$$

The input leakage current on V<sub>SET</sub> is 10 nA maximum. This allows large resistor values to be chosen for R1 and R2 with little degradation in accuracy. For example, a 1 M  $\Omega$  resistor may be selected for R1 and then R2 may be calculated accordingly. The tolerance on V<sub>SET</sub> is guaranteed at less than  $\pm 30$  mV so in most applications, fixed resistors will be suitable.

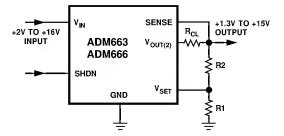


Figure 4. ADM 663/ADM 666 Adjustable Output

#### **Current Limiting**

C urrent limiting may be achieved by using an external current sense resistor in series with  $V_{\text{OUT}(2)}$ . When the voltage across the sense resistor exceeds the internal 0.5 V threshold, current limiting is activated. The sense resistor is therefore chosen such that the voltage across it will be 0.5 V when the desired current limit is reached.

$$R_{CL} = \frac{0.5}{I_{CL}}$$

where R  $_{\text{CL}}\,$  is the current sense resistor, I  $_{\text{CL}}\,$  is the maximum current limit.

The value chosen for  $R_{CL}$  should also ensure that the current is limited to less than the 50 mA absolute maximum rating and also that the power dissipation will also be within the package maximum ratings.

If current limiting is employed, there will be an additional voltage drop across the sense resistor which must be considered when determining the regulators dropout voltage.

If current limiting is not used, the SENSE input should be connected to  $V_{OUT(2)}$ .

#### Shutdown Input (SHDN)

The SHDN input allows the regulator to be switched off with a logic level signal. This will disable the output and reduce the current drain to a low quiescent (12  $\mu$ A maximum) current. This is very useful for low power applications. The SHDN input should be driven with a CMOS logic level signal since the input threshold is 0.3 V. In TTL systems, an open collector driver with a pull-up resistor may be used.

If the shutdown function is not being used, then SHDN  $\,$  should be connected to GND .

#### Low Supply or Low Battery Detection

The ADM 666 contains on-chip circuitry for low power supply or battery detection. If the voltage on the LBI pin falls below the internal 1.3 V reference, then the open drain output LBO will go low. The low threshold voltage may be set to any voltage above 1.3 V by appropriate resistor divider selection.

$$R 3 = R 4 \times \left( \frac{V_{BATT}}{1.30} - 1 \right)$$

where R3 and R4 are the resistive divider resistors and  $V_{\text{BATT}}$  is the desired low voltage threshold.

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## ADM663/ADM666

Since the L B1 input leakage current is less than 10 nA, large values may be selected for R3 and R4 in order to minimize loading. For example, a 6 V low threshold, may be set using 10 M  $\Omega$  for R3 and 2.7 M  $\Omega$  for R4.

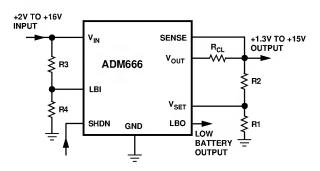


Figure 5. ADM 666 Adjustable Output with Low Battery Detection

#### **High Current Operation**

The ADM 663 contains an additional output,  $V_{\text{OUT1}}$ , suitable for directly driving the base of an external NPN transistor. Figure 6 shows a configuration which can be used to provide +5 V with boosted current drive. A 1  $\Omega$  current sensing resistor limits the current at 0.5 A.

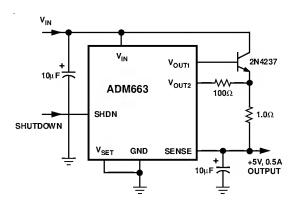


Figure 6. ADM 663 Boosted Output Current (0.5 A)

#### **Temperature Proportional Output**

The ADM 663 contains a  $V_{TC}$  output with a positive temperature coefficient of  $+2.5~\text{mV}/^{\circ}\text{C}$ . This may be connected to the summing junction of the error amplifier ( $V_{SET}$ ) through a resistor resulting in a negative temperature coefficient at the output of the regulator.

This is especially useful in multiplexed LCD displays to compensate for the inherent negative temperature coefficient of the LCD threshold. At 25°C the voltage at the VTC output is typically 0.9 V. The equations for setting both the output voltage and the tempco are given below. If this function is not being used, then  $V_{TC}$  should be left unconnected.

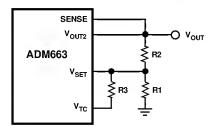


Figure 7. ADM 663 Temperature Proportional Output

$$\begin{aligned} \text{V}_{\text{OUT}} = & \text{V}_{\text{SET}} \times \left(1 + \frac{\text{R 2}}{\text{R 1}}\right) + \frac{\text{R 2}}{\text{R 3}} \times \left(\text{V}_{\text{SET}} - \text{V}_{\text{TC}}\right) \\ & \text{TCV}_{\text{OUT}} = \frac{-\text{R 2}}{\text{R 3}} \times \text{TVC}_{\text{TC}} \\ \text{whereV}_{\text{SET}} = +1.3\text{V} \text{ , V}_{\text{TC}} = +0.9\text{V} \text{ , TCV}_{\text{TC}} = +2.5 \text{ mV} \text{ /}^{\circ}\text{C} \end{aligned}$$

#### **APPLICATION HINTS**

#### Input-Output (Dropout Voltage)

A regulator's minimum input-output differential or dropout voltage determines the lowest input voltage for a particular output voltage. The AD M 663/AD M 666 dropout voltage is 0.8 V at its rated output current. For example when used as a fixed +5 V regulator the minimum input voltage is +5.8 V. At lower output currents, ( $I_{OUT} < 5$  mA), on the AD M 663,  $V_{OUT1}$  may be used as the output driver in order to achieve lower dropout voltages. Please refer to Figure 9. In this case the dropout voltage depends on the voltage drop across the internal FET transistor. This may be calculated by multiplying the FET's saturation resistance by the output current. As the current limit circuitry is referenced to  $V_{OUT2}$ ,  $V_{OUT2}$  should be connected to  $V_{OUT1}$ . For high current operation  $V_{OUT2}$  should be used alone and  $V_{OUT1}$  left unconnected.

#### **Bypass Capacitors**

The high frequency performance of the AD M 663/AD M 666 may be improved by decoupling the output using a filter capacitor. A capacitor value of 10  $\mu$ F is suitable.

An input capacitor helps reduce noise and improves dynamic performance. A suitable input capacitor of 0.1  $\mu F$  or greater may be used.

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## ADM663/ADM666-Typical Performance Characteristics

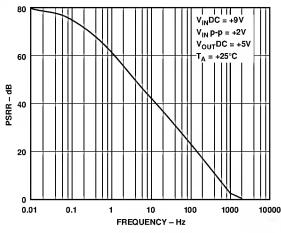


Figure 8. Power Supply Rejection Ratio vs. Frequency

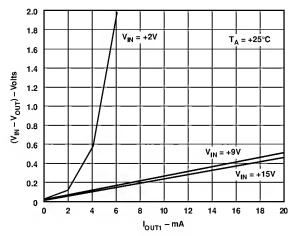


Figure 9.  $V_{OUT1}$  Input-Output Differential vs. Output Current

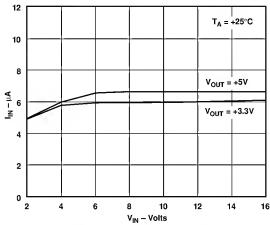


Figure 10. Quiescent Current vs. Input Voltage

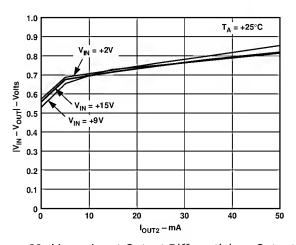
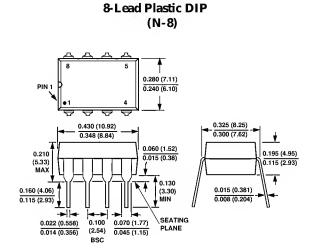


Figure 11.  $V_{OUT(2)}$  Input-Output Differential vs. Output Current

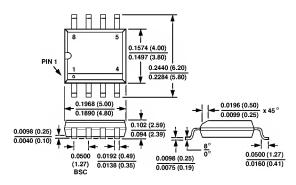
#### **OUTLINE DIMENSIONS**

Dimensions shown in inches and (mm).

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## 8-Lead Narrow-Body (R-8)



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